

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-16. (Cancelled)

17. (Previously Presented) A method of producing a bonded wafer comprising bonding a bond wafer made of silicon single crystal and a base wafer via an oxide film or directly and then reducing thickness of the bond wafer, wherein the base wafer is a wafer produced by processes comprising slicing a silicon single crystal ingot, and then subjected at least to chamfering, lapping, etching, mirror polishing and cleaning, and the etching process is conducted by subjecting the wafer to alkali etching, and then acid etching, and an etching amount in the alkali etching is larger than an etching amount in the acid etching.

18. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein a chamfered part of the base wafer is subjected to a mirror finishing process after the etching process.

19. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein a chamfered part of the base wafer is subjected to a mirror finishing process after bonding the bond wafer to the base wafer.

20. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein an etching process is performed by dipping the wafer in an aqueous solution of hydrogen peroxide after conducting alkali etching, and then conducting acid etching.

21. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein the etching amount is 10 to 30 μm in the alkali etching and 5 to 20 μm in the acid etching.

22. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein the alkali etching solution is an aqueous solution of NaOH or an aqueous

solution of KOH, and the acid etching solution is an aqueous solution of mixed acids comprising hydrofluoric acid, nitric acid, acetic acid and water.

23. (Previously Presented) The method of producing a bonded wafer according to Claim 21 wherein the alkali etching solution is an aqueous solution of NaOH or an aqueous solution of KOH, and the acid etching solution is an aqueous solution of mixed acids comprising hydrofluoric acid, nitric acid, acetic acid and water.

24. (Previously Presented) The method of producing a bonded wafer according to Claim 17 wherein the acid etching is reaction-controlled acid etching.

25. (Previously Presented) The method of producing a bonded wafer according to Claim 24 wherein the solution for reaction-controlled acid etching is an aqueous solution of mixed acids comprising hydrofluoric acid, nitric acid, acetic acid and water in which silicon is dissolved at concentration of 20 to 30 g/l.

26. (Previously Presented) A method of producing a bonded wafer comprising bonding a bond wafer made of silicon single crystal and a base wafer via an oxide film or directly, and then reducing thickness of the bond wafer, wherein the base wafer is a wafer produced by processes comprising slicing a silicon single crystal ingot, and then subjected at least to chamfering, lapping, etching, mirror polishing and cleaning, and the etching process is conducted by subjecting the wafer to acid etching, and the mirror polishing process is conducted on both surfaces.

27. (Previously Presented) The method of producing a bonded wafer according to Claim 26 wherein a chamfered part of the base wafer is subjected to a mirror finishing process after the above-mentioned etching process.

28. (Previously Presented) The method of producing a bonded wafer according to Claim 26 wherein a chamfered part of the base wafer is subjected to a mirror finishing process after bonding a bond wafer to a base wafer.

29. (Previously Presented) A bonded wafer produced by a method according to Claim 17.

30. (Previously Presented) A bonded wafer produced by a method according to Claim 26.

31. (Canceled)

32. (Currently Amended) A bonded wafer produced by a method according to Claim 25, wherein a back surface of its base wafer is chemically etched and a chamfered part is mirror surface, and on the chemically etched back surface, the maximal depth of the pit is $6\mu\text{m}$ or less and the average value of waviness is $0.04\mu\text{m}$ or less.

33. (Currently Amended) A bonded wafer produced by a method according to Claim 17, wherein a power spectrum density waviness having a wavelength of 10 mm on a back surface of its base wafer is 0.5 to $10\mu\text{m}^3$ as power spectrum density measured by waviness having a wavelength of 10 mm.

34. (Canceled)

35. (New) A bonded wafer produced by a method according to Claim 18.

36. (New) A bonded wafer produced by a method according to Claim 19.

37. (New) A bonded wafer produced by a method according to Claim 20.

38. (New) A bonded wafer produced by a method according to Claim 27.

39. (New) A bonded wafer produced by a method according to Claim 28.